ABSTRACT OF THE DISCLOSURE

A novel design for an electrode for a thin film transistor. The novel design allows for formation of a normal conductive channel between a source electrode and a drain electrode even after a heat treatment process, and a flat panel display including the thin film transistor. The thin film transistor includes a source electrode, a drain electrode, a gate electrode, and a semiconductor layer, wherein at least one of the source electrode, the drain electrode, and the gate electrode includes an aluminum alloy layer, and titanium layers are formed on both surfaces of the aluminum alloy layer. The electrodes are preferably absent any pure aluminum as pure aluminum can diffuse into the semiconductor layer causing a defect region and preventing a conductive channel from forming in the thin film transistor.